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# **Quad 2-Input Exclusive OR Gate with LSTTL Compatible Inputs**

## **High-Performance Silicon-Gate CMOS**

The MC74HCT86A is identical in pinout to the LS86. The device inputs are compatible with standard CMOS outputs and LSTTL outputs.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with JEDEC Standard No. 7A Requirements
- Chip Complexity: 56 FETs or 14 Equivalent Gates
- These are Pb-Free Devices

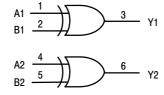
## **PIN ASSIGNMENT**

14	v <sub>cc</sub>
13	] B4
12	A4
11	] Y4
10	] B3
9	] A3
8	] Y3
	13 12 11 10 9

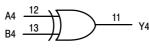
## **FUNCTION TABLE**

Inp	Output	
Α	Υ	
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

## **LOGIC DIAGRAM**







 $Y = A \oplus B$ PIN 14 = V<sub>CC</sub> PIN 7 = GND  $= \overline{A}B + A\overline{B}$ 



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**MARKING DIAGRAMS** 



PDIP-14 **N SUFFIX** CASE 646





SOIC-14 **D SUFFIX CASE 751A** 



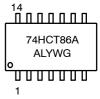


TSSOP-14 **DT SUFFIX** CASE 948G





SOEIAJ-14 **F SUFFIX CASE 965** 



= Assembly Location

L. WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

## **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GN	ID)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND	)	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GN	D)	- 0.5 to V <sub>CC</sub> + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	± 20	mA	
l <sub>out</sub>	DC Output Current, per Pin	± 25	mA	
Icc	DC Supply Current, V <sub>CC</sub> and GND Pin	DC Supply Current, V <sub>CC</sub> and GND Pins		mA
$P_{D}$		ssipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†		mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C	
TL	Lead Temperature, 1 mm from Case for (Plastic DIP, SOIC or TS:		260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)			6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V	
T <sub>A</sub>	Operating Temperature, All Package Types	Operating Temperature, All Package Types			°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $V_{CC} = 2.0$ (Figure 1) $V_{CC} = 4.5$ $V_{CC} = 6.0$	V	0 0 0	1000 500 400	ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 to 5.5	2.0	2.0	2.0	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 to 5.5	0.8	0.8	0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL} $ $ I_{out}  \leq 4.0 \text{ mA}$	4.5	3.98	3.84	3.70	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	٧
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad  I_{out}  \leq 4.0 \text{ mA}$	4.5	0.26	0.33	0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	± 0.1	± 1.0	± 1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	1.0	10	40	μΑ

## AC ELECTRICAL CHARACTERISTICS (CL = 50 pF, Input t, = $t_f$ = 6 ns, $V_{CC}$ = 5.0 V $\pm$ 10%)

				Gu	aranteed Li	mit	
Symbol	Parameter		V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	t <sub>PLH</sub> t <sub>PHL</sub>	5.0 5.0	20 17	25 21	31 26	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)		5.0	15	19	22	ns
C <sub>in</sub>	Maximum Input Capacitance			10	10	10	pF
				Typical	@ 25°C, V <sub>C</sub>	<sub>C</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Gate)*				33		pF

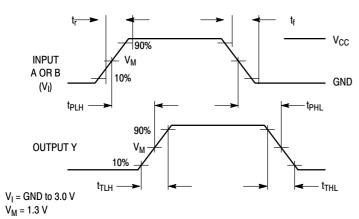
<sup>\*</sup>Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74HCT86ANG	PDIP-14 (Pb-Free)	25 Units / Rail
MC74HCT86ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HCT86ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74HCT86ADTR2G	TSSOP-14*	·
MC74HCT86AFG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74HCT86AFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*This package is inherently Pb-Free.



TEST

TEST

TEST

\*Includes all probe and jig capacitance

DEVICE UNDER OUTPUT

TEST POINT

Figure 1. Switching Waveforms

Figure 2. Test Circuit

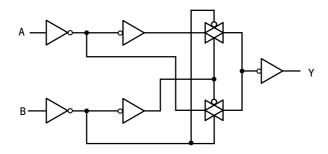
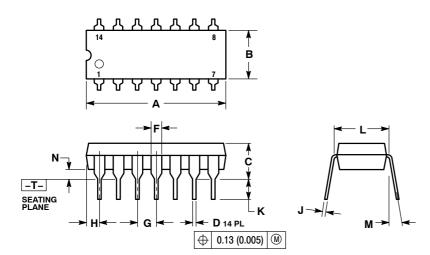


Figure 3. Expanded Logic Diagram (1/4 of Device)

## **PACKAGE DIMENSIONS**

PDIP-14 CASE 646-06 **ISSUE P** 

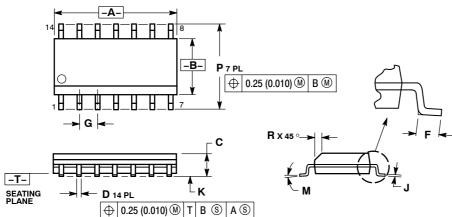


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
М		10 °		10 °
N	0.015	0.039	0.38	1.01

## PACKAGE DIMENSIONS

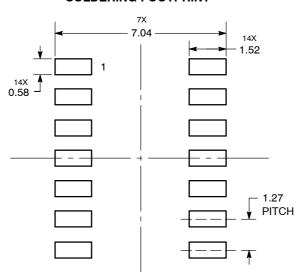
SOIC-14 CASE 751A-03 **ISSUE J** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

## **SOLDERING FOOTPRINT\***

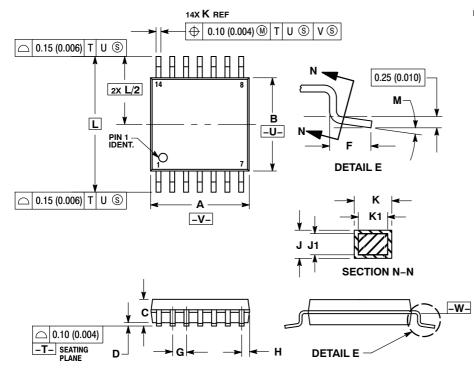


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## PACKAGE DIMENSIONS

## TSSOP-14 CASE 948G-01 **ISSUE B**

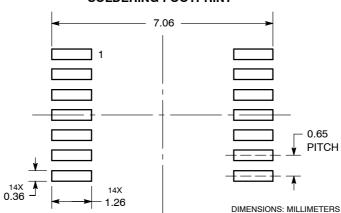


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
   DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
- CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE

PETE	RMINED AT DATUM PLANE -W MILLIMETERS INCHES					
			INC			
DIM	MIN	MAX	MIN	MAX		
Α	4.90	5.10	0.193	0.200		
В	4.30	4.50	0.169	0.177		
С		1.20		0.047		
D	0.05	0.15	0.002	0.006		
F	0.50	0.75	0.020	0.030		
G	0.65	BSC	0.026	BSC		
H	0.50	0.60	0.020	0.024		
J	0.09	0.20	0.004	0.008		
J1	0.09	0.16	0.004	0.006		
K	0.19	0.30	0.007	0.012		
K1	0.19	0.25	0.007	0.010		
L	6.40	BSC	0.252	BSC		
М	0 °	8 °	0 °	8 °		

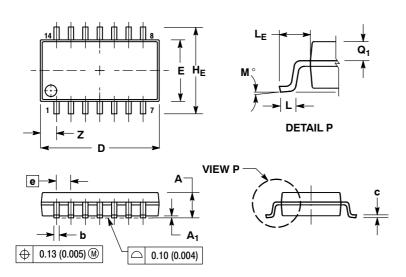
## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 **ISSUE B** 



#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- I. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- i. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

  DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0°	10 °
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		1.42		0.056

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